

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

On page 1, after the title of the application, please insert the following section:

This application is a §371 national phase filing of PCT/CH2005/000184 filed March 31, 2005, and claims priority to European application No. 04007760.4 filed March 31, 2004.

Please amend the paragraph on page 7, line 30 through page 8, line 8, as follows:

The method according to the invention for sensing incident radiation comprises the steps of: converting the incident radiation into charge carriers of a first and a second charge type in an active area of a semiconductor material processed on one side only, generating a lateral electric field at the semiconductor surface in said active area for separating said charge carriers of the first charge type from said charge carriers of the second charge type, and storing charge carriers of at least one charge type in a charge-storage area which is laterally adjacent to said active area, but geometrically separated and ~~electrically~~ electrically isolated from said active area. Said lateral electric field is a steplike lateral electric field.

Please amend the paragraph on page 17, line 27 through page 18,
line 2, as follows:

In the dynamic operation mode, the pixel according to the invention is illuminated with radiation In modulated with a given modulation frequency. Such modulated radiation, preferably in the radio-frequency (RF) range, may be emitted by a light source allocated to the image sensor, and reflected by objects in the scene to be sensed. The steplike lateral electric field is periodically changed, so that charge carriers are stored in at least two charge-storage areas which are laterally adjacent to the active area, but geometrically separated and electrically electrically isolated from the active area.